

Original

Am99C164/Am99CL164 Am99C165/Am99CL165

16,384 x 4 Static R/W Random-Access Memory

PRELIMINARY

Am99C164/Am99CL164
Am99C165/Am99CL165

Advanced Micro Devices

DISTINCTIVE CHARACTERISTICS

- Fast access time - 35/45/55/70 ns maximum
- 16K x 4 organization
- Output Enable (\overline{OE}) control to alleviate bus-contention conditions (Am99C165)
- Single 5-V $\pm 10\%$ power-supply operation
- Fully static storage and interface circuitry
- Automatic power-down when deselected
- Low power dissipation
 - 550 mW operating power
 - 200 μ W data retention
- 2-V data-retention capability
- 22-pin 0.300-inch DIP (Am99C164)
- 22-pin LCC (Am99C164)
- 24-pin 0.300-inch DIP (Am99C165)
- 28-Pin LCC (Am99C165)

GENERAL DESCRIPTION

The Am99C164 and Am99C165 are high-performance 16,384 x 4-bit static random-access memories (RAMs) manufactured with state-of-the-art CMOS processing techniques.

The Am99C164 device features common input/output pins and two control signals, \overline{CE} and \overline{WE} . While \overline{CE} controls read, write, and selection/deselection of the device, \overline{WE} controls the write operation and output buffers only.

The Am99C165 device features three control signals (\overline{CE} , \overline{WE} , and \overline{OE}) to facilitate not only memory expansion, but also alleviate any bus-contention conditions which might limit high-performance read/write operation. While \overline{WE} activates only the input buffers during a write cycle, \overline{OE} activates only the output buffers during a read cycle. \overline{CE} in

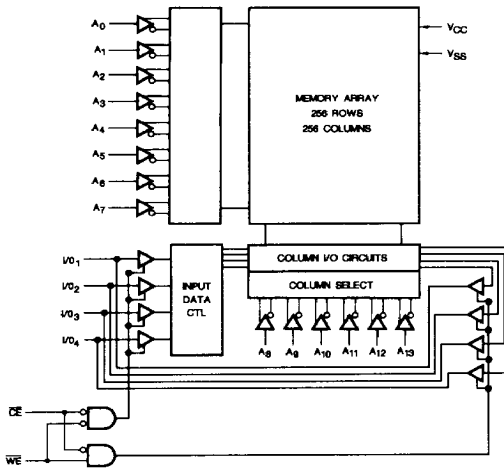
the HIGH state deselects the entire device and reduces power consumption. All input/output interface levels are fully TTL-compatible for both the Am99C164 and Am99C165.

The Am99C164 and Am99C165 require a single 5-volt power supply while operating but can hold the data when power-supply level is maintained at a voltage as low as 2 volts.

The Am99C164 is available in 22-pin 0.300-inch wide ceramic and plastic DIPs, and 22-pin rectangular ceramic leadless chip carriers. The Am99C165 is available in 24-pin 0.300-inch wide ceramic and plastic DIPs, and 28-pin rectangular ceramic leadless chip carriers.

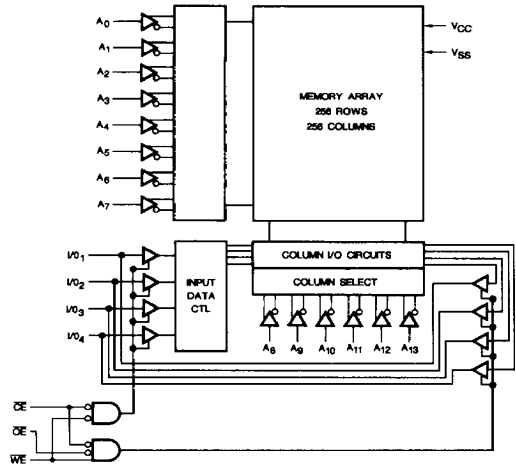
BLOCK DIAGRAM

Am99C164



BD005702

Am99C165



BD005712

3

Rev

Orig

004781

1

4781

Publication #	Rev.	Amendment
07437	E	/0
Issue Date: June 1987		

PRODUCT SELECTOR GUIDE

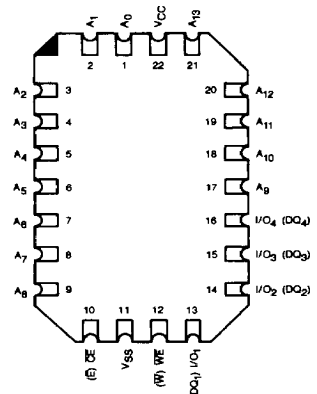
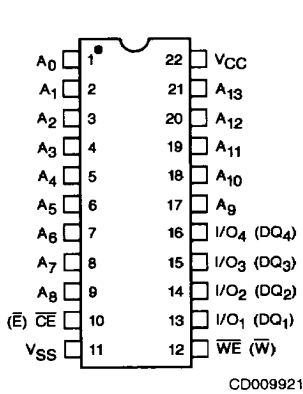
Family Part No.		Am99C164/Am99CL164 Am99C165/Am99CL165					
Ordering Part No.		-35	-45	-55	-70		
Access Time (ns)		35	45	55	70		
Commercial (C) Devices: 0 to +70°C	Symbol	Power*					
	I _{CC} (mA)	S	110	110	110	110	
		L	105	95	90	90	
	I _{SB1} (mA)	S	45	45	45	45	
		L	25	25	25	25	
	I _{SB2} (mA)	S	25	25	25	25	
		L	20	20	20	20	
	I _{SB3} (mA)	S	15	15	15	15	
		L	0.3	0.3	0.3	0.3	
	I _{CCDR} (mA) @ 2 V	S	-	-	-	-	
		L	0.1	0.1	0.1	0.1	
	Extended Commercial (E) and Military (M) Devices -55 to +125°C	I _{CC} (mA)	S	-	120	120	120
			L	-	110	105	105
		I _{SB1} (mA)	S	-	50	50	50
L			-	30	30	30	
I _{SB2} (mA)		S	-	35	35	35	
		L	-	25	25	25	
I _{SB3} (mA)		S	-	20	20	20	
		L	-	1.0	1.0	1.0	
I _{CCDR} (mA) @ 2 V		S	-	-	-	-	
		L	-	0.3	0.3	0.3	

*S = Standard Power (Am99C164, Am99C165)
L = Low Power (Am99CL164, Am99CL165)

CONNECTION DIAGRAMS

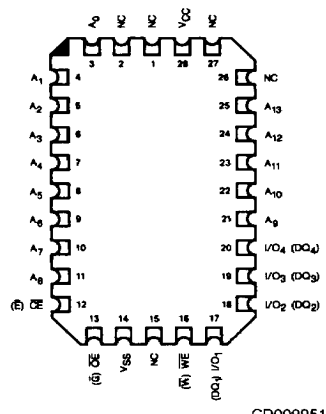
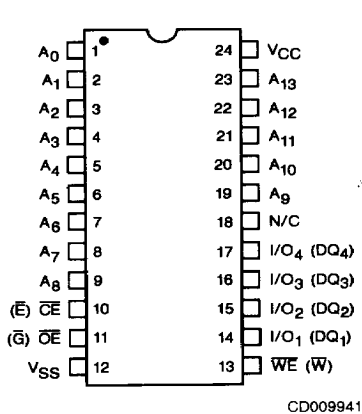
Top View

Am99C164/Am99CL164



Note: Pin 1 is marked for orientation.

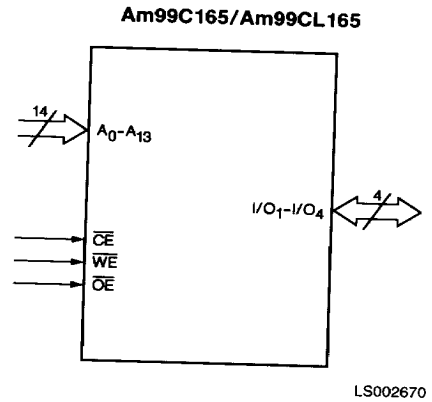
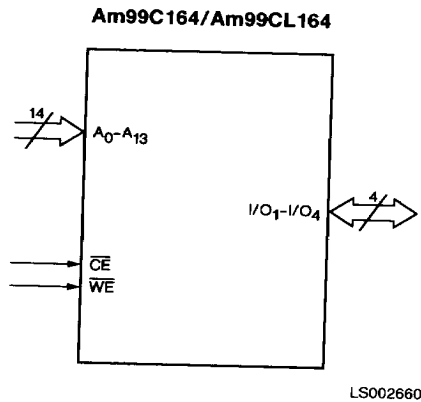
Am99C165/Am99CL165



Note: Pin 1 is marked for orientation.

IEEE Nomenclature in Brackets.

LOGIC SYMBOLS



Address Designators

External	Internal*	Pin Number DIP Package
A ₀	AX ₅	1
A ₁	AX ₆	2
A ₂	AX ₃	3
A ₃	AX ₄	4
A ₄	AX ₇	5
A ₅	AY ₀	6
A ₆	AY ₁	7
A ₇	AY ₂	8
A ₈	AY ₃	9
A ₉	AY ₄	17, 19*
A ₁₀	AY ₅	18, 20*
A ₁₁	AX ₀	19, 21*
A ₁₂	AX ₂	20, 22*
A ₁₃	AX ₃	21, 23*

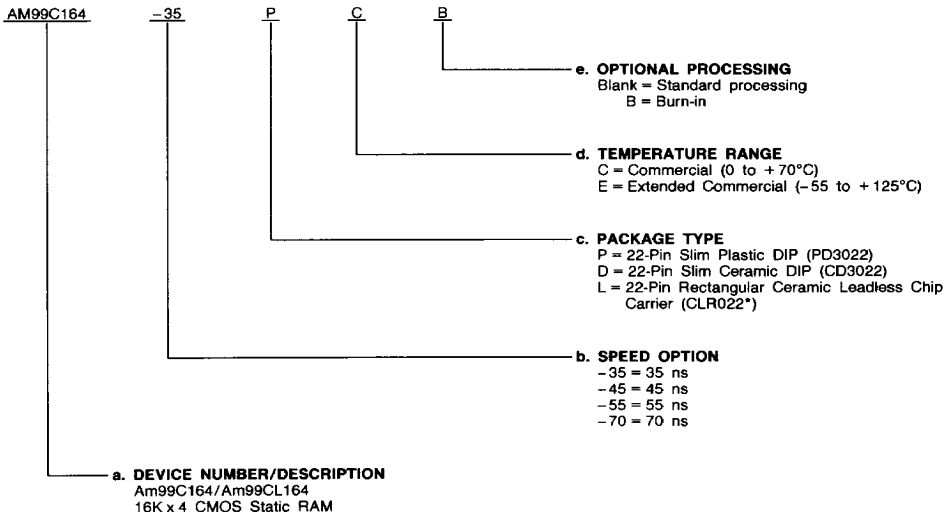
*For Am99C165, Am99CL165

ORDERING INFORMATION — Am99C164

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:

- a. **Device Number**
- b. **Speed Option** (if applicable)
- c. **Package Type**
- d. **Temperature Range**
- e. **Optional Processing**



*Preliminary. Subject to change.

Valid Combinations	
AM99C164-35	PC, PCB, DC,
AM99CL164-35	DCB, LC, LCB
AM99C164-45	PC, PCB, DC, DCB, DE, DEB, LC, LCB, LE, LEB
AM99CL164-45	
AM99C164-55	
AM99CL164-55	
AM99C164-70	
AM99CL164-70	

Valid Combinations

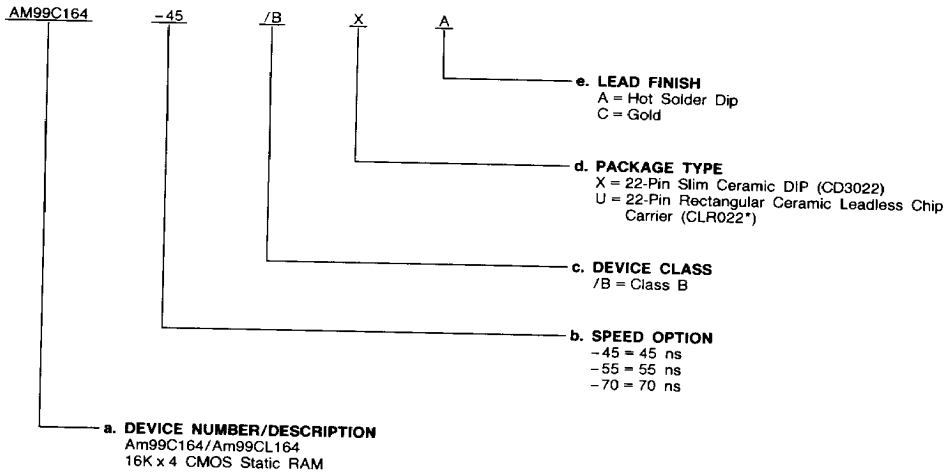
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

ORDERING INFORMATION — Am99C164 (Cont'd.)

APL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) for APL products is formed by a combination of:

- a. **Device Number**
- b. **Speed Option** (if applicable)
- c. **Device Class**
- d. **Package Type**
- e. **Lead Finish**



*Preliminary. Subject to change.

Valid Combinations	
AM99C164-45	/BXA, /BXC, /BUA
AM99CL164-45	
AM99C164-55	
AM99CL164-55	
AM99C164-70	
AM99CL164-70	

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

Group A Tests

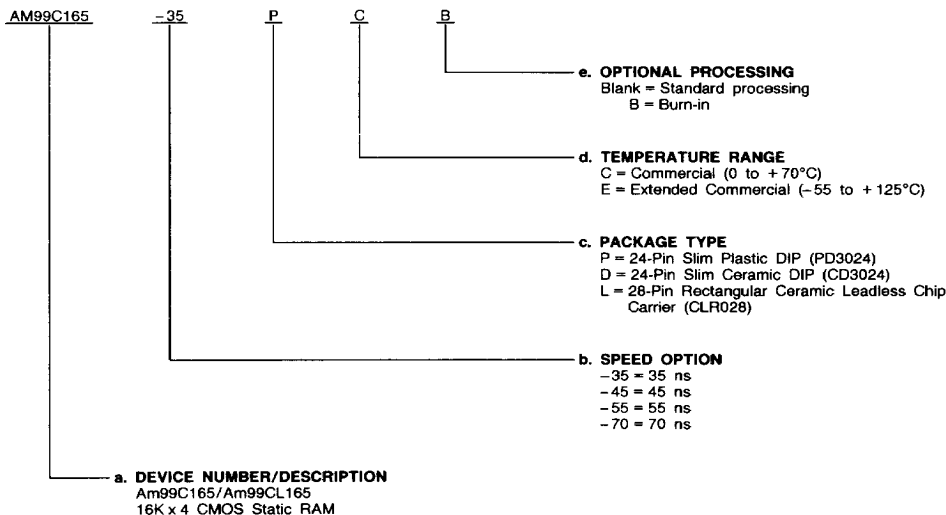
Group A tests consist of Subgroups
1, 2, 3, 7, 8, 9, 10, 11

ORDERING INFORMATION — Am99C165

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:

- a. **Device Number**
- b. **Speed Option** (if applicable)
- c. **Package Type**
- d. **Temperature Range**
- e. **Optional Processing**



Valid Combinations	
AM99C165-35	PC, PCB, DC, DCB, LC, LCB
AM99CL165-35	
AM99C165-45	PC, PCB, DC, DCB, DE, DEB, LC, LCB, LE, LEB
AM99CL165-45	
AM99C165-55	
AM99CL165-55	
AM99C165-70	
AM99CL165-70	

Valid Combinations

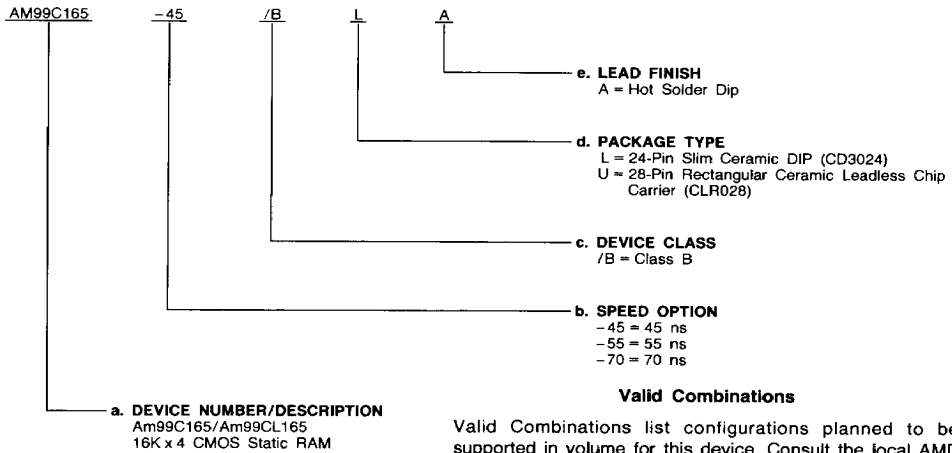
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

ORDERING INFORMATION — Am99C165 (Cont'd.)

APL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) for APL products is formed by a combination of:

- a. Device Number
- b. Speed Option (if applicable)
- c. Device Class
- d. Package Type
- e. Lead Finish



Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

Valid Combinations	
AM99C165-45	/BLA, /BUA
AM99CL165-45	
AM99C165-55	
AM99CL165-55	
AM99C165-70	
AM99CL165-70	

Group A Tests

Group A tests consist of Subgroups 1, 2, 3, 7, 8, 9, 10, 11

PIN DESCRIPTION

A₀ - A₁₃ Address Lines (Input)

The address input lines select the RAM location to be read from or written into.

CE Chip Enable (Input, Active LOW)

CE selects the memory device. WE is ignored when CE is HIGH.

WE Write Enable (Input, Active LOW)

When WE is LOW and CE is also LOW, data will be written into the location specified on the address pins. When WE is

HIGH and CE is LOW (and OE is LOW for Am99C165) data will be read out and placed on the I/O pin.

OE Output Enable (Input, Active LOW)

When OE is LOW, it activates the output buffers during a read cycle, for Am99C165 only.

I/O₁ - I/O₄ Data In/Out Bus (Input/Output)

These I/O lines provide the path for data to be read from or written into the selected memory location.

V_{CC} +5-Volt Power Supply

V_{SS} 0-Volt Ground

ABSOLUTE MAXIMUM RATINGS (Note 1)

Storage Temperature	
Ceramic DIPs & LCCs	-65 to +150°C
Plastic DIPs	-55 to +125°C
Ambient Temperature with Power Applied	
Ceramic DIPs & LCCs	-65 to +135°C
Plastic DIPs	-10 to +85°C
DC Supply Voltage	
to Ground Potential Continuous	-0.5 to +7.0 V
All Signal Voltages	-0.5 to +7.0 V
DC Output Current	20 mA
Power Dissipation	1.0 W

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES (Note 2)

Commercial (C) Devices	
Temperature (T _A)	0 to +70°C
Supply Voltage (V _{CC})	4.5 to +5.5 V
Extended Commercial (E) and Military (M) Devices	
Temperature (T _A)	-55 to +125°C
Supply Voltage (V _{CC})	+4.5 to +5.5 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating range unless otherwise specified (for APL Products, Group A, Subgroups 1, 2, 3 are tested unless otherwise noted)

Parameter Symbol	Parameter Description	Test Conditions	Min.	Max.	Units
I _{OH}	Output HIGH Current	V _{OH} = 2.4 V, V _{CC} = 4.5 V	-4		mA
I _{OL}	Output LOW Current	V _{OL} = 0.4 V	8		mA
V _{IH}	Input HIGH Voltage		2.2	V _{CC} + 1.0	V
V _{IL}	Input LOW Voltage	Note 8	-0.5	0.8	V
I _{Ix}	Input Load Current	GND ≤ V _{IN} ≤ V _{CC}		2.0	μA
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , CE ≥ V _{IH}		2.0	μA

DC CHARACTERISTICS over Commercial (0 to +70°C) Operating Range*

Parameter Symbol	Parameter Description	Test Conditions	Power**	Am99C164/Am99CL164 Am99C165/Am99CL165				Unit
				-35	-45	-55	-70	
I _{CC}	Dynamic Operating Supply Current	Cycle = Min., Duty = 100%, CE ≤ V _{IL} , I/O = 0 mA	S	110	110	110	110	mA
			L	105	95	90	90	
I _{CC1}	Static Operating Supply Current	CE ≤ V _{IL} , I/O = 0 mA	S	80	80	80	80	mA
			L	60	60	60	60	
I _{SB1}	Standby Current, Cycling TTL Levels	CE ≥ V _{IH} ; V _{CC} = Max., Cycle = Min.	S	45	45	45	45	mA
			L	25	25	25	25	
I _{SB2}	Standby Current, Stable TTL Levels	CE ≥ V _{IH} , V _{IN} ≥ V _{IH} or ≤ V _{IL}	S	25	25	25	25	mA
			L	20	20	20	20	
I _{SB3}	Standby Current, Stable CMOS Input Levels	CE ≥ V _{CC} - 0.2 V, V _{IN} ≥ V _{CC} - 0.2 V or ≤ 0.2 V	S	15	15	15	15	mA
			L	0.3	0.3	0.3	0.3	

Notes: See notes following Capacitance table on the following page.

- *All values are guaranteed maximum limits.
- **S = Standard Power (Am99C164/Am99C165)
- L = Low Power (Am99CL164/Am99CL165)

* L
* S

DC CHARACTERISTICS over Extended Commercial and Military (-55 to +125°C) Operating Ranges*

Parameter Symbol	Parameter Description	Test Conditions	Power**	Am99C164/Am99CL164 Am99C165/Am99CL165			Unit
				-45	-55	-70	
I _{CC}	Dynamic Operating Supply Current	Cycle = Min., Duty = 100%, $\overline{CE} \leq V_{IL}$, I/O = 0 mA	S	120	120	120	mA
			L	110	105	105	
I _{CC1}	Static Operating Supply Current	$\overline{CE} \leq V_{IL}$, I/O = 0 mA	S	100	100	100	mA
			L	80	80	80	
I _{SB1}	Standby Current, Cycling TTL Levels	$\overline{CE} \geq V_{IH}$, V _{CC} = Max., Cycle = Min.	S	50	50	50	mA
			L	30	30	30	
I _{SB2}	Standby Current, Stable TTL Levels	$\overline{CE} \geq V_{IH}$, V _{IN} = V _{IH} or $\leq V_{IL}$	S	35	35	35	mA
			L	25	25	25	
I _{SB3}	Standby Current, Stable CMOS Input Levels	$\overline{CE} \geq V_{CC} - 0.2$ V, V _{IN} $\geq V_{CC} - 0.2$ V or ≤ 0.2 V	S	20	20	20	mA
			L	1.0	1.0	1.0	

*All values are guaranteed maximum limits.

**S = Standard Power (Am99C164/Am99C165)

L = Low Power (Am99CL164/Am99CL165)

CAPACITANCE†






Parameter Symbol	Parameter Description	Test Conditions	Min.	Max.	Units
C _I ††	Input Capacitance Except \overline{CE}	f = 1 MHz, V _{IN} = 0 V		7	pF
C _O ††	Output Capacitance	V _{OUT} = 0 V		7	
\overline{CE} ††	Chip Enable Input Capacitance	f = 1 MHz, V _{IN} = 0 V		7.5	pF

† These capacitances are not 100% tested, but are evaluated at initial characterization and at any time the product is modified where capacitance may be affected. Measurement performed at T_A = +25°C.

†† = Not included in Group A tests.

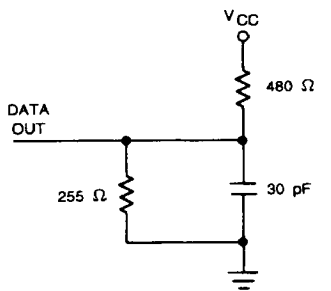
- Notes:
1. Absolute Maximum Ratings are intended for user guidelines and are not tested.
 2. For test and correlation purposes, operating temperature is defined as the "instant-on" case temperature.
 3. Parameter not tested—guaranteed by characterization.
 4. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5 V, input-pulse levels of 0 to 3.0 V, and output loading of specified I_{OL}/I_{OH} and 30-pF load capacitance. Output timing reference is 1.5 V (see Test Load A in Switching Test Circuits section).
 5. The internal write time of the memory is defined by the overlap of \overline{CE} active and \overline{WE} LOW. Both signals must be active to initiate a write and either signal can terminate a write by going inactive. The data input setup and hold timing should be referenced to the transition edge that terminates the write.
 6. The minimum limit is not tested and is included for design information only.
 7. Parameter not tested, guaranteed by characterization using the load shown in Test Load B—Switching Test Circuits. Transition is measured ± 500 mV from steady state voltage.
 8. Undershoot to -3.0 V for a duration of 10 ns between the 50% amplitude points is permissible.
 9. Address input rise and fall times must not exceed 1 μ s when \overline{CE} is active. This limit is not tested and is intended for design information only.

KEY TO SWITCHING WAVEFORMS

WAVEFORM	INPUTS	OUTPUTS
	MUST BE STEADY	WILL BE STEADY
	MAY CHANGE FROM H TO L	WILL BE CHANGING FROM H TO L
	MAY CHANGE FROM L TO H	WILL BE CHANGING FROM L TO H
	DON'T CARE: ANY CHANGE PERMITTED	CHANGING: STATE UNKNOWN
	DOES NOT APPLY	CENTER LINE IS HIGH IMPEDANCE 'OFF' STATE

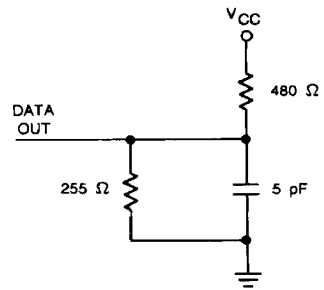
KS000010

SWITCHING TEST CIRCUITS



TC003163

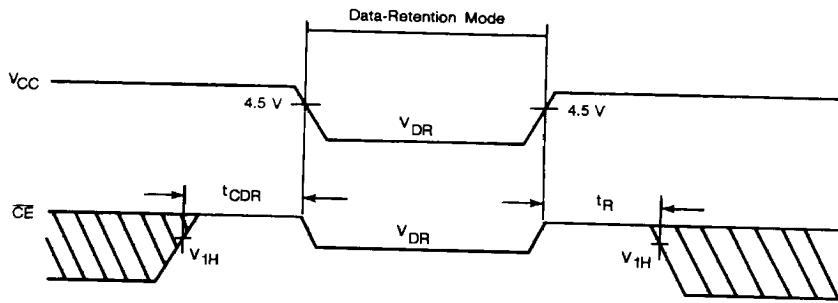
Test Load A



TC003173

Test Load B

SWITCHING TEST WAVEFORM



WF021434

Low V_{CC} Data Retention Characteristics (Low-Power Version Only)

Parameter Symbol	Parameter Description	Test Conditions	Min.	Max.	Units
V_{DR}	V_{CC} for Data Retention	$\overline{CE} \geq V_{CC} - 0.2 \text{ V}$	2.0		V
I_{CCDR}	Data Retention Current	$V_{CC} = 2 \text{ V}$	COM'L	0.1	mA
			MIL	0.3	
I_{CCDR}	Data Retention Current	$V_{CC} = 3 \text{ V}$	COM'L	0.15	mA
			MIL	0.45	
t_{CDR}	Chip Deselect to Data Retention Time (Note 1)	See Waveform (Note 2)	0		ns
t_R	Operating Recovery Time (Note 1)		t_{RC}		ns

- Notes: 1. Parameter not tested, guaranteed by design.
 2. Waveforms shown are not actual and may vary in use.

SWITCHING CHARACTERISTICS over operating range unless otherwise specified (for APL Products, Group A, Subgroups 7, 8, 9, 10, 11 are tested unless otherwise noted)

No.	Parameter Symbols	Parameter Description	Am99C164/Am99CL164 Am99C165/Am99CL165								Units	
			-35		-45		-55		-70			
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
READ CYCLES ONE, TWO, AND THREE (Note 9)												
1	t _{ELQV}	t _{ACS}	Chip Enable Access Time		35		45		55		70	ns
2	t _{AVAV}	t _{RC}	Read Cycle Time	35		45		55		70		ns
3	t _{AVQV}	t _{AA}	Address Access Time		35		45		55		70	ns
4	t _{AXQX}	t _{OH}	Output Hold After Address	5		5		5		5		ns
5†	t _{ELQX}	t _{LZ}	Chip Enable to Output Active (Note 7)	5		5		5		5		ns
6†	t _{EHQZ}	t _{HZ}	Chip Disable to Output Disable (Note 7)		15		15		20		25	ns
7†	t _{ELICCH}	t _{PU}	Chip Enable to Power Up (Note 3)	0		0		0		0		ns
8†	t _{EHICCL}	t _{PD}	Chip Disable to Power Down (Note 3)	0	35	0	45	0	55	0	70	ns
WRITE CYCLES ONE AND TWO (Note 9)												
9†	t _{AVAV}	t _{WC}	Write Cycle Time	35		45		55		70		ns
10†	t _{WLWH}	t _{WP}	Write Pulse Width (Note 5)	30		40		50		60		ns
11†	t _{ELWH}	t _{CW}	Chip Enable to End of Write (Note 5)	35		40		50		60		ns
12	t _{DVWH}	t _{DW}	Data Setup to End of Write	20		25		30		30		ns
13†	t _{WHDX}	t _{DH}	Data Hold After End of Write	0		0		0		0		ns
14†	t _{AVWH}	t _{AW}	Address Setup to End of Write (Note 5)	30		40		50		60		ns
15	t _{AVWL}	t _{AS}	Address Setup to Beginning of Write	0		0		0		0		ns
16	t _{WHAX}	t _{WR}	Address Hold After End of Write	0		0		0		0		ns
17†	t _{WLQZ}	t _{WZ}	Write Enable to Output Disable (Notes 6 & 7)	0	10	0	15	0	20	0	25	ns
18†	t _{WHQX}	t _{OW}	Output Active After End of Write (Notes 6 & 7)	5		5		5		5		ns
19†	t _{GLQV}	t _{OE}	Output Enable Access Time (Am99C165/Am99CL165 only)		15		20		25		30	ns

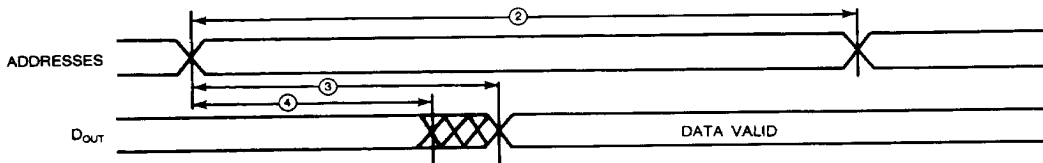
SWITCHING CHARACTERISTICS (Cont'd.)

No.	Parameter Symbols		Parameter Description	Am99C164/Am99CL164 Am99C165/Am99CL165								Units
				-35		-45		-55		-70		
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
20†	t _{GLQX}	t _{OLZ}	Output Enable to Output Active (Am99C165/Am99CL165 only) (Note 7)	5		5		5		5		ns
21†	t _{GHQZ}	t _{OHZ}	Output Enable to Output Disable (Am99C165/Am99CL165 only) (Note 7)	0	15	0	15	0	15	0	15	ns

- Notes:
1. Absolute Maximum Ratings are intended for user guidelines and are not tested.
 2. For test and correlation purposes, operating temperature is defined as the "instant-on" case temperature.
 3. Parameter not tested—guaranteed by characterization.
 4. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5 V, input-pulse levels of 0 to 3.0 V, and output loading of specified I_{OL}/I_{OH} and 30-pF load capacitance. Output timing reference is 1.5 V (see Test Load A in Switching Test Circuits section).
 5. The internal write time of the memory is defined by the overlap of \overline{CE} active and \overline{WE} LOW. Both signals must be active to initiate a write and either signal can terminate a write by going inactive. The data input setup and hold timing should be referenced to the transition edge that terminates the write.
 6. The minimum limit is not tested and is included for design information only.
 7. Parameter not tested, guaranteed by characterization using the load shown in Test Load B—Switching Test Circuits. Transition is measured ± 500 mV from steady state voltage.
 8. Undershoot to -3.0 V for a duration of 10 ns between the 50% amplitude points is permissible.
 9. Address input rise and fall times must not exceed 1 μ s when \overline{CE} is active. This limit is not tested and is intended for design information only.

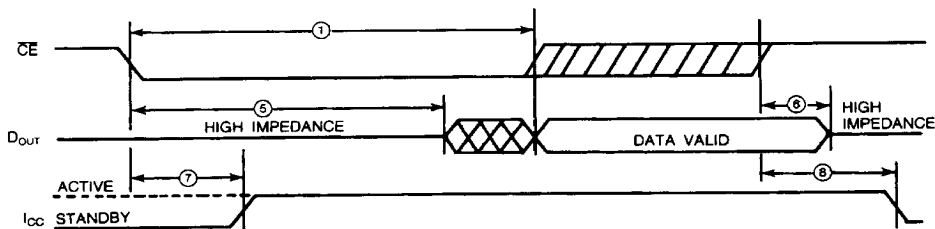
† Not included in Group A tests

SWITCHING WAVEFORMS



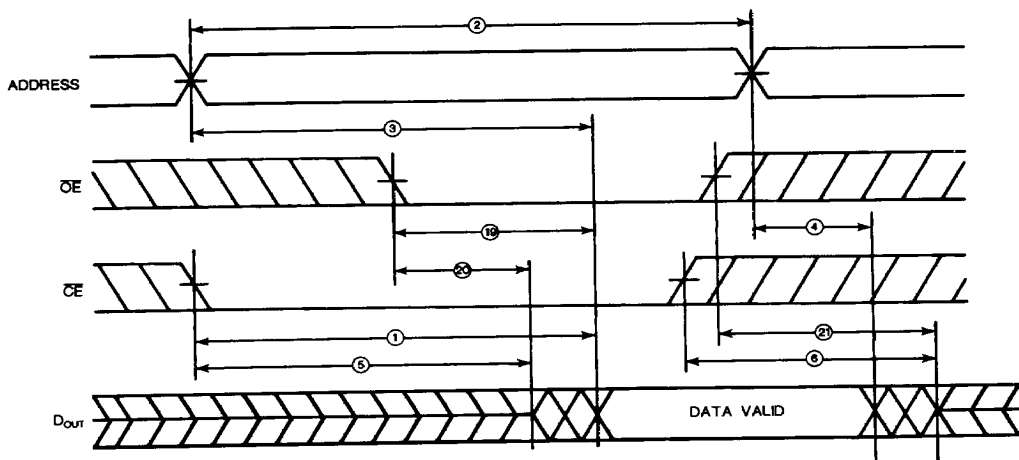
WF021460

Read Cycle One (Notes 1, 2, & 4)



WF021472

Read Cycle Two (Notes 1, 3, & 4)

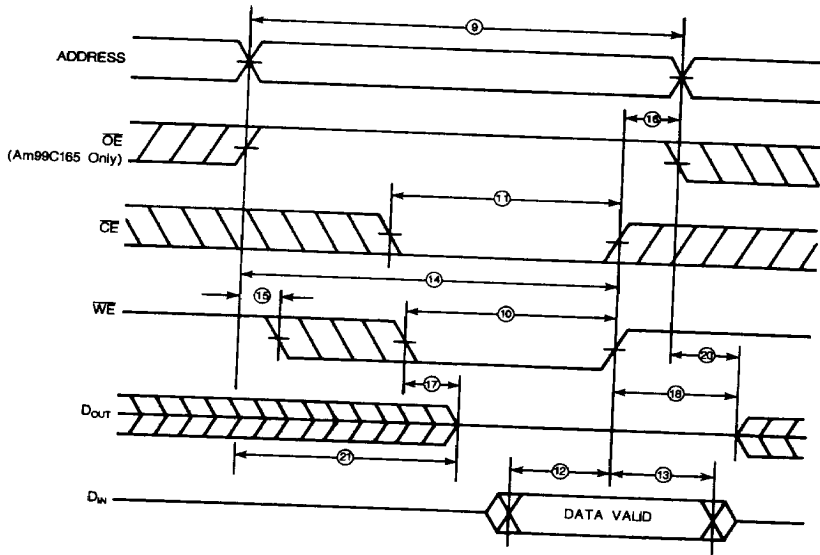


WF022492

**Read Cycle Three (Notes 1 & 3)
(Am99C165/Am99CL165 Only)**

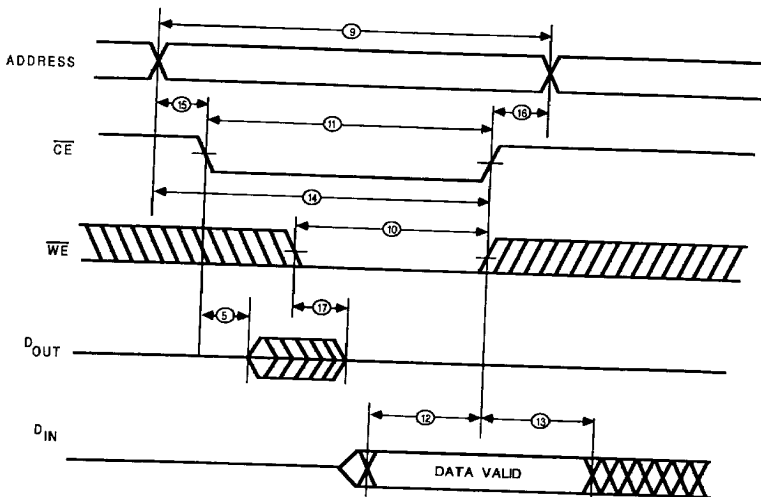
- Notes:
1. \overline{WE} is HIGH for Read Cycle.
 2. \overline{CE} is LOW for Read Cycle.
 3. Address Valid prior to or coincident with \overline{OE} transition LOW.
 4. $\overline{OE} = V_{IL}$ (Am99C165/Am99CL165 only)

SWITCHING WAVEFORMS (Cont'd.)



WF022503

Write Cycle One (\overline{WE} -Controlled) (Notes 1 & 3)



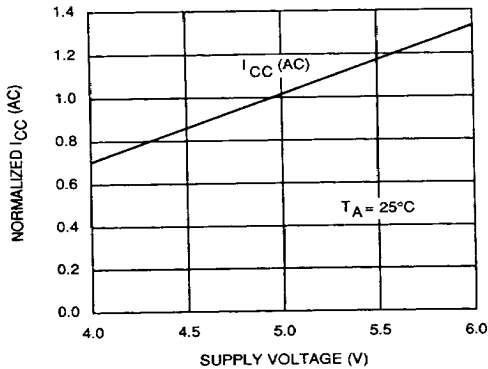
WF023263

Write Cycle Two (\overline{CE} -Controlled) (Notes 1, 2, & 3)

- Notes:
1. \overline{WE} or \overline{CE} must be HIGH during all address transitions.
 2. \overline{OE} is continuously LOW ($\overline{OE} = V_{IL}$) for Am99C165.
 3. If \overline{CE} LOW transition occurs simultaneously with \overline{WE} LOW transition or after \overline{WE} transition, outputs remain in a high-impedance state.

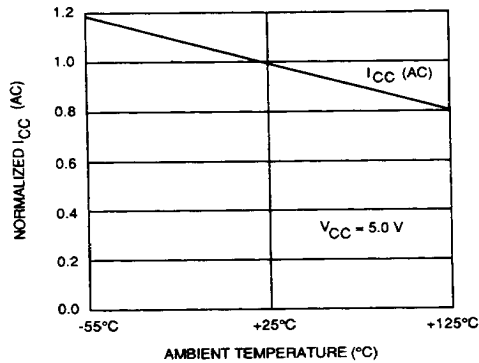
TYPICAL PERFORMANCE CURVES

NORMALIZED SUPPLY CURRENT vs SUPPLY VOLTAGE



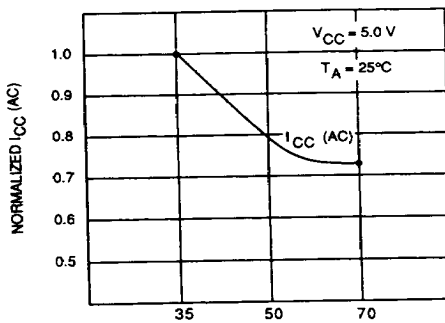
OP002510

NORMALIZED SUPPLY CURRENT vs AMBIENT TEMPERATURE



OP002380

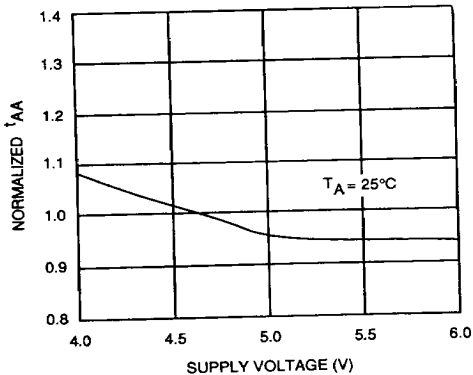
NORMALIZED $I_{CC} (AC)$ vs CYCLE TIME



CYCLE TIME (ns)

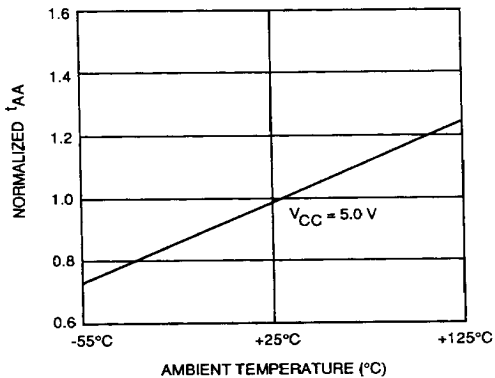
OP002390

NORMALIZED ACCESS TIME vs SUPPLY VOLTAGE



OP002520

NORMALIZED ACCESS TIME vs AMBIENT TEMPERATURE

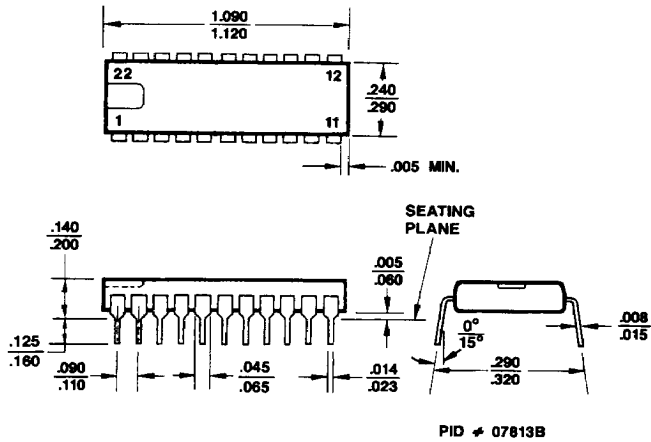


OP002530

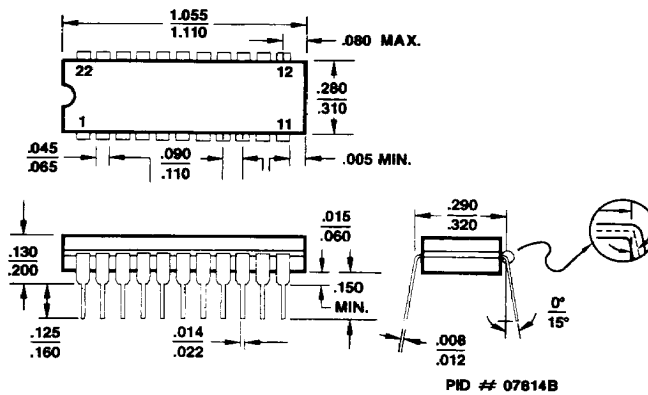
PHYSICAL DIMENSIONS*

Am99C164

PD3022



CD3022



*For reference only.

